

Oki Semiconductor develops low-power single-chip EML driver IC for 40 Gbps optical communications

- Targets more than 50% market share with world-leading small size, low power consumption and XLMD-MSA support -

TOKYO, March 19, 2009 – Oki Semiconductor Co., Ltd. announces the development of a new product, the KGA8205, a single-chip EML(*1) driver IC that can be mounted on a 40Gbps EML based on XLMD-MSA(*2). The KGA8205 features small size and low power consumption of 1.1W (amplitude 2.3Vpp).

Sample of the products are available now and volume shipment is scheduled to start from June 2009.



The KGA8205 is provided in die form, allowing direct EML connection without the need to add external output bias circuit components. The chip size is small, 1.8mm x 1.2 mm, and the pad configuration complies with XLMD-MSA specifications, making this product ideal for EML modules based on XLMD-MSA with built-in drivers. This product uses InP HEMT (*3) device offering excellent high-speed characteristics, achieving high-speed operation and low power consumption of 1.1 W (2.3 Vpp output amplitude) for 43 Gbps operation.

This IC generates high-quality optical waveforms for use in 40 Gbps optical communications EML, and also facilitates size and power consumption reductions. Oki Semiconductor will continue to develop and deliver high-performance, high-quality optical communications driver IC to the optical communications IC market.

The 40 Gbps EML driver will be exhibited and explained at the Oki Semiconductor booth (#2431) at the Optical Fiber Communications Conference & Exposition and the National Fiber Optic Engineers Conference (OFC/NFOEC2009) (http://www.ofcnfoec.org/) joint venue to be held in San Diego, California, March 22 to 26 (Sun. to Thur.), 2009.

Sales Plan

- Sample shipment: March 2009
- Volume shipment: June 2009
- Sales target: > 50% of market share by fiscal 2010.

Main features

- 43 Gbps operation
- 2.3 Vpp output amplitude (typical)
- 1.1 W (typical)
- 1.8 mm x 1.2 mm (chip size)

Glossary

*1: EML (electro-absorption modulated laser)

Optical semiconductor component integrating laser diode and electro-absorption optical modulator

*2: XLMD-MSA

Multi-source agreement for 40 Gbps optical communications transmitter and receiver modules

*3: InP HEMT

Compound semiconductor device using 2-dimensional electron gas layer for channel on InP compound semiconductor substrate, offering outstanding high-speed performance.

* Names of companies and products are trademarks or registered trademarks of the respective companies and organizations.

Press Contact:

Public Relations and Corporate Brand Office Phone: +81-42-662-0209 E-mail: press@adm.okisemi.com